



High-Speed CMOS 4K x 36 Block-Allocated Shared-Port RAM with Flexi-Burst™

QS75436

FEATURES

- Two independent 2K x 36-bit blocks
- Independent port controls
- Fast port access times: 20 ns, 25 ns, 30 ns
- 50-MHz, 40-MHz, 33-MHz cycle times
- Total bandwidth 3.6 Gbits/sec
- Simultaneous access for different block operations
- Clocked/pipelined and Flexi-Burst™
- Built-in busy arbitration logic for each block
- Low-power QCMOS™ technology
- Separate byte enables for accessing 9-, 18-, 27-, 36-bit words
- Available in 208-pin QFP

DESCRIPTION

This device consists of two blocks of 2K x 36 bits SRAM which can be accessed from either port using the independent port control pins. Each port has a clocked interface in which addresses, data and control are loaded on the rising edge of the relevant clock. The data can be pipelined or burst depending upon the state of the control pins. This can allow for very fast block transfers of 3.6 Gbits/sec in burst mode with both ports active. Arbitration is done on a block basis with a BKBSY (Block Busy) flag. This will lock out the losing port and allow access to the winning port to write or read to that block. If non-coincidental blocks are addressed, then both ports can access their respective blocks. Applications for this part are datacomms, ATM, networking, multimedia and graphics.

FIGURE 1. FUNCTIONAL BLOCK DIAGRAM

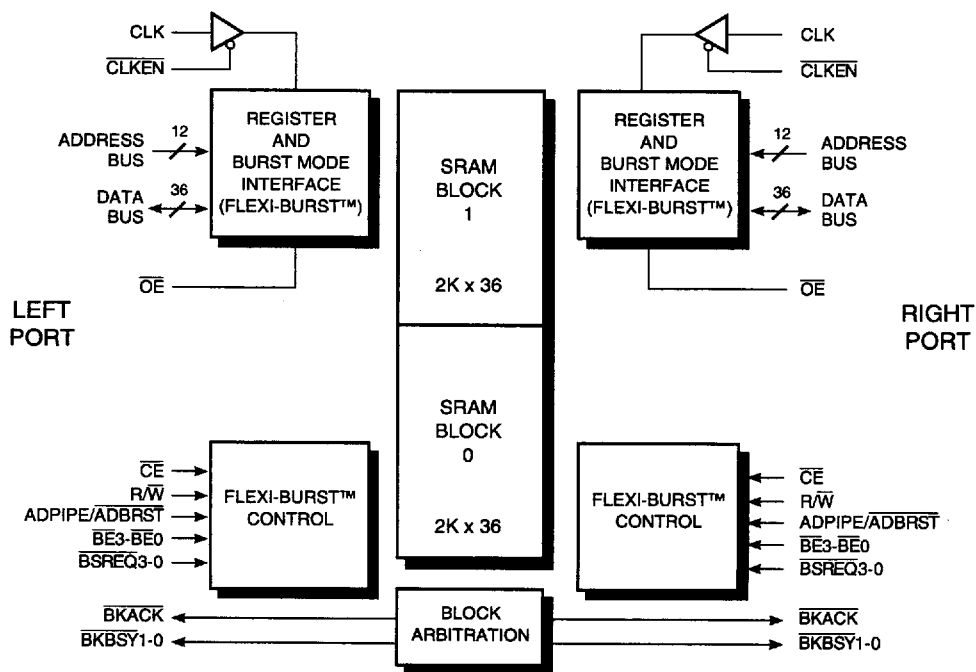
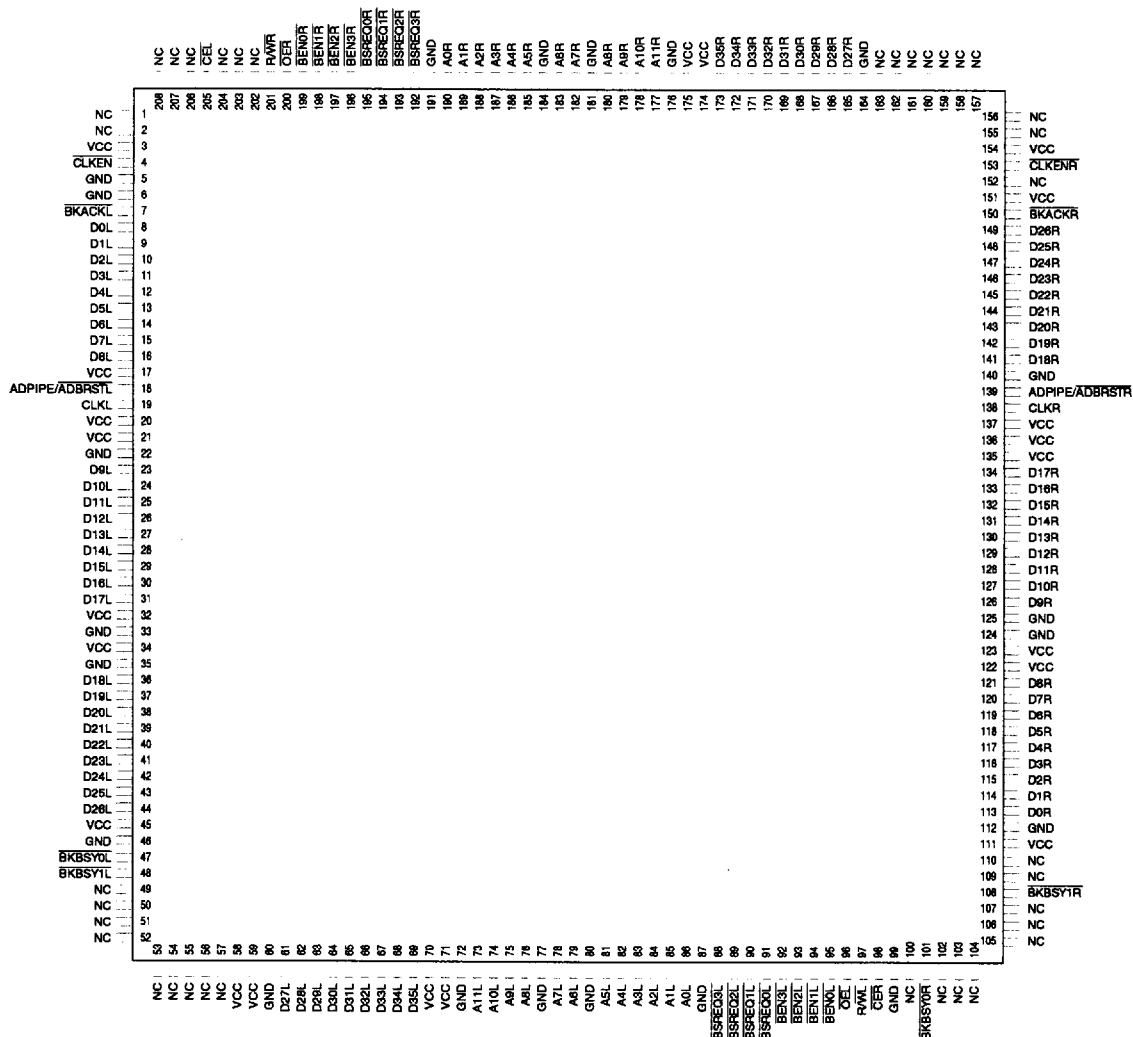


FIGURE 2. 208-PIN QFP PINOUT

PIN DESCRIPTIONS

Pin Name Left Port	Pin Name Right Port	Status	Pins/Port	Pin Description
ADD _L	ADD _R	I	12	Address Bus
DATA _L	DATA _R	I/O	36	Data Bus
CE _L	CE _R	I	1	Chip Enable
R/W _L	R/W _R	I	1	Read/Write
CLK _L	CLK _R	I	1	Clock
CLKEN _L	CLKEN _R	I	1	Clock Enable
OE _L	OE _R	I	1	Output Enable
ADPIPE/ADBRST _L	ADPIPE/ADBRST _R	I	1	Address Pipelined/Burst Mode Select
BE3-BE0 _L	BE3-BE0 _R	I	4	Byte Enable
BSREQ _L 3-0	BSREQ _R 3-0	I	4	Burst Block Size Request
BKBSY _L 1-0	BKBSY _R 1-0	O	2	Block Busy Flag
BKACK _L	BKACK _R	O	1	Burst Block Complete Acknowledge

ADDRESS (12-Bit Address Bus, Left and Right Port)

The independent port address bus allows the SRAM blocks to be accessed on the rising edge of the relevant port clock.

DATA (36-Bit Bi-directional Data Ports, Left and Right)

This is a 36-bit wide data bus. The left port data bus is designated DATA_L; similarly, the right port is designated DATA_R. The data is sampled on the rising edge of the relevant port clock. When BSREQ3-0 is set to "1111," then the data bus D10-D0 can be used to program the block burst size to any value.

CLK (Clock)

Each port has its own free-running clock. If both port addresses are simultaneously clocked and are of the same value, the BKBSY output will be asserted synchronously to the winning port clock.

CLKEN (Clock Enable)

Each port has its own clock enable. When asserted, allows the port to be clocked; when de-asserted, no operation is performed.

ADPIPE/ADBRST (Address Pipelined/Address Burst Mode Select)

When asserted HIGH with a valid address synchronous with the rising edge of the relevant port clock, the address is clocked in to the relevant SRAM block.

When asserted LOW with a valid address synchronous with the rising edge of the relevant port clock, along with the BSREQ value, the data can be burst on every rising edge of the associated port clock. The internal burst counter alleviates the need to provide external subsequent addresses. This counter is a full wraparound counter.

BSREQ (Burst Size Request)

This is a 4-bit signal which when asserted in the address phase along with ADPIPE/ADBRST sets the value of the burst block size, be it a read or write transaction; (see BURST BLOCK SIZE TRUTH TABLE). When set all to "1," then the value on the data bus preloads the burst size to the binary value.

BURST BLOCK SIZE TRUTH TABLE

BSREQ3	BSREQ2	BSREQ1	BSREQ0	Burst Block Size x 36-Bit Words
0	0	0	0	2
0	0	0	1	4
0	0	1	0	8
0	0	1	1	16
0	1	0	0	32
0	1	0	1	64
0	1	1	0	128
0	1	1	1	256
1	0	0	0	512
1	0	0	1	1024
1	0	1	0	2048
1	1	1	1	Value placed on the Data Bus D10-D0

EXAMPLE OF FLEXI-BURST

BSREQ3	BSREQ2	BSREQ1	BSREQ0	Burst Block Size x 36-Bit Words	Data Bus D10-D0
1	1	1	1	48 words	000 0011 0000
1	1	1	1	53 words	000 0011 0101
1	1	1	1	106 words	000 0110 1010

$\overline{OE}$ (Output Enables)

There are two output enables $\overline{OE_L}$ and $\overline{OE_R}$ that are asynchronous active LOW inputs. When asserted LOW, the output buffers place data on the respective data bus.

$\overline{BKACK}$ (Block Acknowledge)

This asserts in burst mode only and indicates when the end of block has been reached.

$\overline{BKBSY}$ (Block Busy)

Whenever any port wins access to an SRAM block, a $\overline{BKBSY}$ signal is asserted to prevent the losing port from accessing the same SRAM block. Each SRAM block has a pair of busy flags, one for each port. This signal is cleared when the winning port relinquishes control of that block by changing the address to a different block or by the use of $\overline{CE}$. This signal is synchronous to the winning port clock.

$\overline{CE}$ (Chip Enable)

Each port has an active LOW synchronous chip enable. This input, when asserted synchronously with the respective port clock, allows access to the RAM array blocks. The busy arbitration is reset when $\overline{CE}$ is clocked HIGH, allowing access to all the blocks.

$R/\overline{W}$ (Read/Write)

Each port has its own synchronous read/write input. Read operations are performed when this signal is HIGH at the rising edge of its respective port clock. Write operations are performed when the signal is sampled in the LOW state.

$\overline{BE}$ (Byte Enables 0..3)

There are four byte enables for each port. All signals are synchronous to its respective port clock. These signals allow byte, half-word, tri-byte and word transfers to and from the SRAM blocks. This method allows for efficient connecting of differing bus sizes of 9, 18, 27, 36 bits.

ABSOLUTE MAXIMUM RATINGS

Supply Voltage to Ground	-0.5 to 7.0V
DC Output Voltage V_{OUT}	-0.5 to $V_{CC} + 0.5V$
DC Input Voltage V_{IN}	-0.5 to $V_{CC} + 0.5V$
AC Input Voltage (Pulse Width $\leq 10ns$)	-1.5V
DC Input Diode Current with $V_{IN} < 0$	-20 mA
DC Output Diode Current with $V_{OUT} < 0$	-50 mA
DC Output Current with $V_{OUT} > V_{CC}$	50 mA
DC Output Current Max Sink Current/Pin	70 mA
T_{STG} Storage Temperature	-55°C to +125°C

Note: Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to this device, resulting in functional- or reliability-type failures.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Commercial: $T_A = 0^\circ C$ to $70^\circ C$, $V_{CC} = 5.0V \pm 10\%$

Symbol	Parameter	Test Conditions	Min	Max	Units
V_{IH}	Input HIGH Voltage	Logic HIGH for all Inputs	2.0	—	V
V_{IL}	Input LOW Voltage	Logic LOW for all Inputs	—	0.8	V
V_{OH}	Output HIGH Voltage	$I_{OH} = -4$ mA, $V_{CC} = \text{Min.}$	2.4	—	V
V_{OL}	Output LOW Voltage	$I_{OL} = 4$ mA, $V_{CC} = \text{Min.}$	—	0.4	V
I_{IL}	Input Leakage	$V_{CC} = \text{Max.}$, $V_{IN} = \text{GND or } V_{CC}$	—	100	μA

Notes:

1. Transient inputs with V_{IL} not more negative than -1.5V are permitted for pulse widths < 10 ns.
2. Input leakage also includes I/Os.

CAPACITANCE

$T_A = 25^\circ C$, $f = 1.0$ MHz QFP (QF) package

Name	Description	Conditions	Typ	Max	Units
C_{IN}	Input Capacitance	$V_{IN} = 0V$	10	15	pF
C_{OUT}	Output Capacitance	$V_{OUT} = 0V$	10	15	pF

Note: Capacitance is guaranteed but not tested.

POWER SUPPLY CHARACTERISTICS

Symbol	Parameter	Cycle Time, ns (MHz)						Units
		-20 (50)		-25 (40)		-30 (33)		
		Typ	Max	Typ	Max	Typ	Max	
Icc1	Operating Current Vcc = Max, Outputs Open f = fMAX	400	450	320	350	264	288	mA

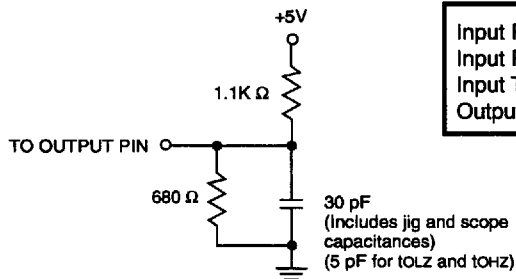
AC CHARACTERISTICS -20 ns (50 MHz)

Symbol	Parameter	Min	Max	Units
t _{CLKL}	Clock Low Time	8		ns
t _{CLKH}	Clock High Time	8		ns
t _{CYC}	Cycle Time	20		ns
t _{OLZ}	Output Enable to LOW-Z ⁽¹⁾		14	ns
t _{OHZ}	Output Enable to HIGH-Z ⁽¹⁾		14	ns
t _{OE}	Output Enable Time		14	ns
t _{DS}	Data Setup Time	5		ns
t _{DH}	Data Hold Time	2		ns
t _{CDO}	Clock High to Output Valid	4	15	ns
t _{AS}	Address Setup Time	5		ns
t _{AH}	Address Hold Time	2		ns
t _{RWS}	Read/Write Setup Time	5		ns
t _{RWH}	Read/Write Hold Time	2		ns
t _{CKS}	Clock Enable Setup Time	5		ns
t _{CKH}	Clock Enable Hold Time	2		ns
t _{BES}	Byte Enable Setup Time	5		ns
t _{BEH}	Byte Enable Hold Time	2		ns
t _{PBS}	Pipeline/Burst Setup Time	5		ns
t _{PHB}	Pipeline/Burst Hold Time	2		ns
t _{BSY}	Clock to Busy	10	17	ns
t _{CES}	Chip Enable Setup Time	5		ns
t _{CEH}	Chip Enable Hold Time	2		ns

Note:

1. Guaranteed but not tested.

FIGURE 3. AC TEST CONDITIONS



Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	≤ 3 ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V

AC CHARACTERISTICS -25 ns (40 MHZ)

Symbol	Parameter	Min	Max	Units
tCLKL	Clock Low Time	12		ns
tCLKH	Clock High Time	12		ns
tCYC	Cycle Time	25		ns
tOLZ	Output Enable to LOW-Z ⁽¹⁾		16	ns
tOHZ	Output Enable to HIGH-Z ⁽¹⁾		16	ns
tOE	Output Enable Time		16	ns
tDS	Data Setup Time	8		ns
tDH	Data Hold Time	2		ns
tCDO	Clock High to Output Valid	4	17	ns
tAS	Address Setup Time	8		ns
tAH	Address Hold Time	2		ns
tRWS	Read/Write Setup Time	8		ns
tRWH	Read/Write Hold Time	2		ns
tCKS	Clock Enable Setup Time	8		ns
tCKH	Clock Enable Hold Time	2		ns
tBES	Byte Enable Setup Time	8		ns
tBEH	Byte Enable Hold Time	2		ns
tPBS	Pipeline/Burst Setup Time	8		ns
tPHB	Pipeline/Burst Hold Time	2		ns
tBSY	Clock to Busy	9	18	ns
tCES	Chip Enable Setup Time	8		ns
tCEH	Chip Enable Hold Time	2		ns

AC CHARACTERISTICS -30 ns (33 MHZ)

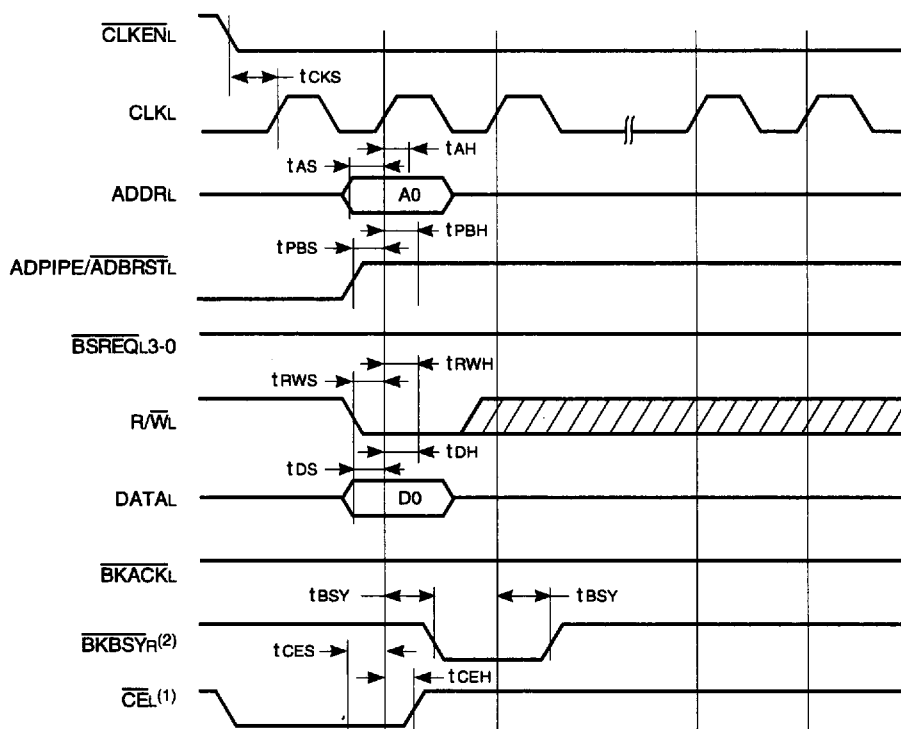
Symbol	Parameter	Min	Max	Units
tCLKL	Clock Low Time	15		ns
tCLKH	Clock High Time	15		ns
tCYC	Cycle Time	30		ns
tOLZ	Output Enable to LOW-Z ⁽¹⁾		17	ns
tOHZ	Output Enable to HIGH-Z ⁽¹⁾		17	ns
tOE	Output Enable Time		17	ns
tDS	Data Setup Time	9		ns
tDH	Data Hold Time	1		ns
tCDO	Clock High to Output Valid	4	20	ns
tAS	Address Setup Time	9		ns
tAH	Address Hold Time	1		ns
tRWS	Read/Write Setup Time	9		ns
tRWH	Read/Write Hold Time	1		ns
tCKS	Clock Enable Setup Time	9		ns
tCKH	Clock Enable Hold Time	1		ns
tBES	Byte Enable Setup Time	9		ns
tBEH	Byte Enable Hold Time	1		ns
tPBS	Pipeline/Burst Setup Time	9		ns
tPHB	Pipeline/Burst Hold Time	1		ns
tBSY	Clock to Busy	10	19	ns
tCES	Chip Enable Setup Time	9		ns
tCEH	Chip Enable Hold Time	1		ns

Note:

1. Guaranteed but not tested.

TIMING DIAGRAMS

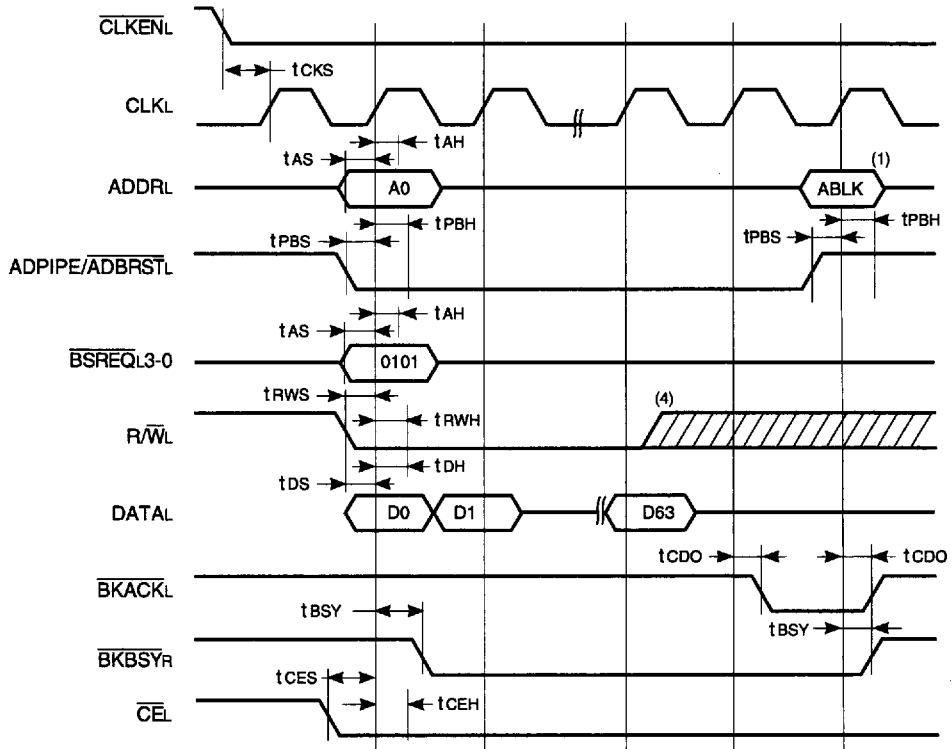
FIGURE 4. SINGLE WORD WRITE, ONE PORT, ONE BLOCK USING $\overline{\text{CE}}$ TO RESET BKBSY



Notes:

1. If $\overline{\text{CEL}} = \text{H}$ on the next CLOCKL , the $\overline{\text{BKBSYr}}$ signals will be reset.
2. $\overline{\text{BKBSYr}}$ will also be reset if the port address is moved to another block and clocked.

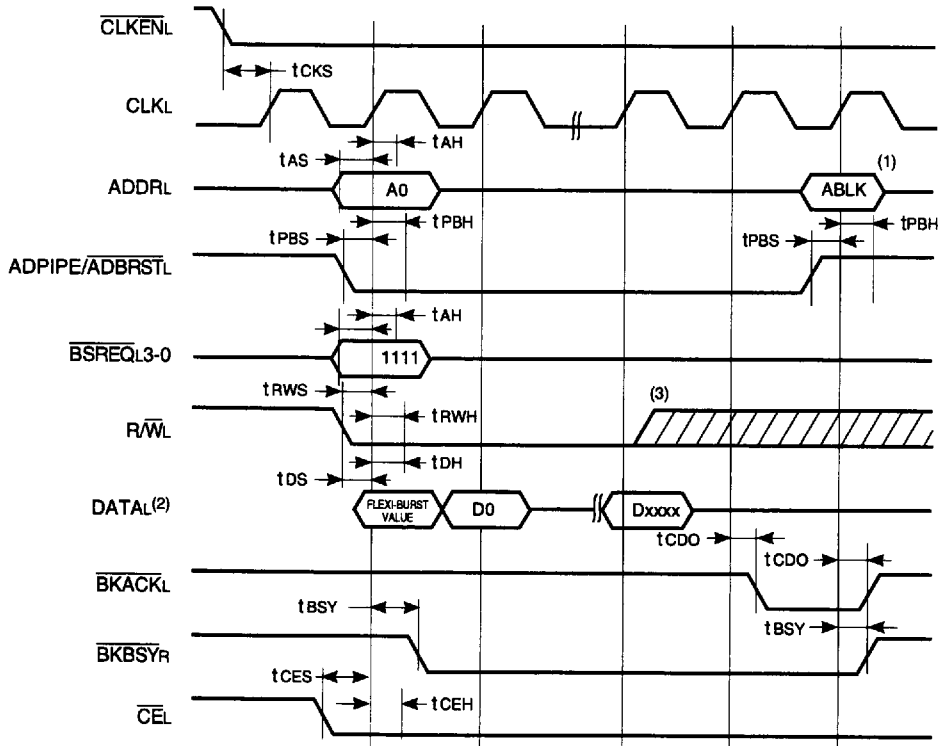
FIGURE 5. BURST WRITE ONE PORT, ONE BLOCK



Notes:

1. The address (ABLK) can be any address which is not in the block to reset control of that respective SRAM block and allow the other port to take control if requested.
2. The burst block size is set up from the BURST BLOCK SIZE TRUTH TABLE, p. 7-6.
3. BKACKl going LOW prevents any further burst writes.
4. Must satisfy trwh at last burst clock.

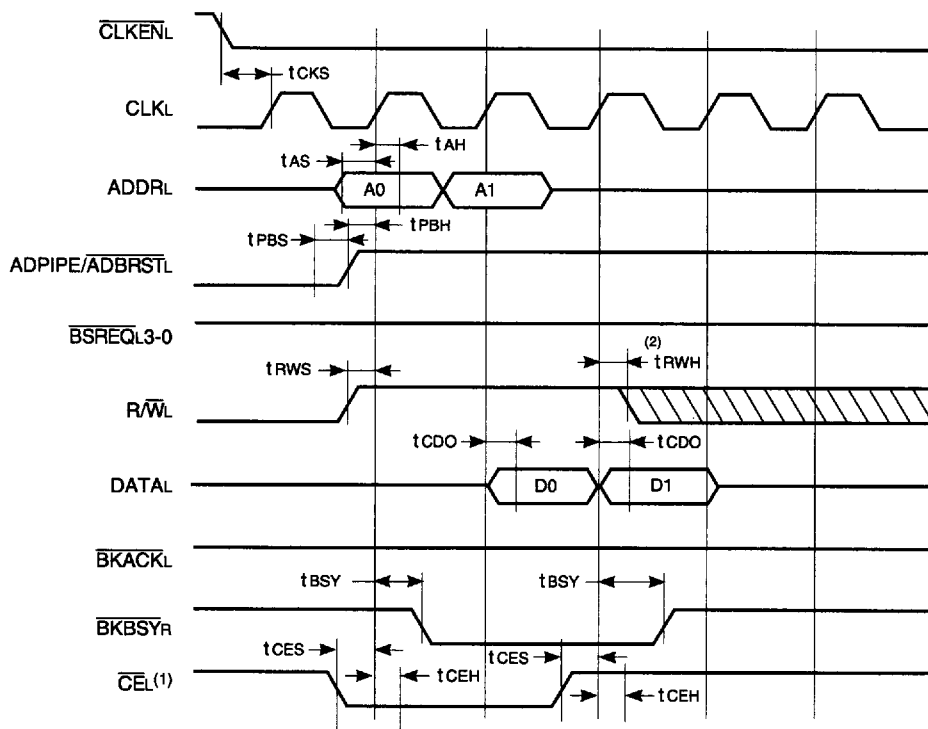
FIGURE 6. FLEXI-BURST WRITE ONE PORT, ONE BLOCK



Notes:

1. The address (ABLK) can be any address which is not in the block to reset control of that respective SRAM block and allow the other port to take control if requested.
2. Binary value placed on data bus D11-D0 sets up burst block size
3. Must satisfy t_{RWH} at last burst clock.

FIGURE 7. SINGLE-WORD PIPELINED READS, ONE BLOCK USING $\overline{CE}$ TO RESET $\overline{BKBSY}$



Notes:

1. If $\overline{CE} = H$ on the next $CLOCK_L$ the $\overline{BKBSY}_R$ signals will be reset.
2. Must satisfy t_{RWH} at last burst clock.

FIGURE 8. TWO READS FOLLOWED BY A WRITE

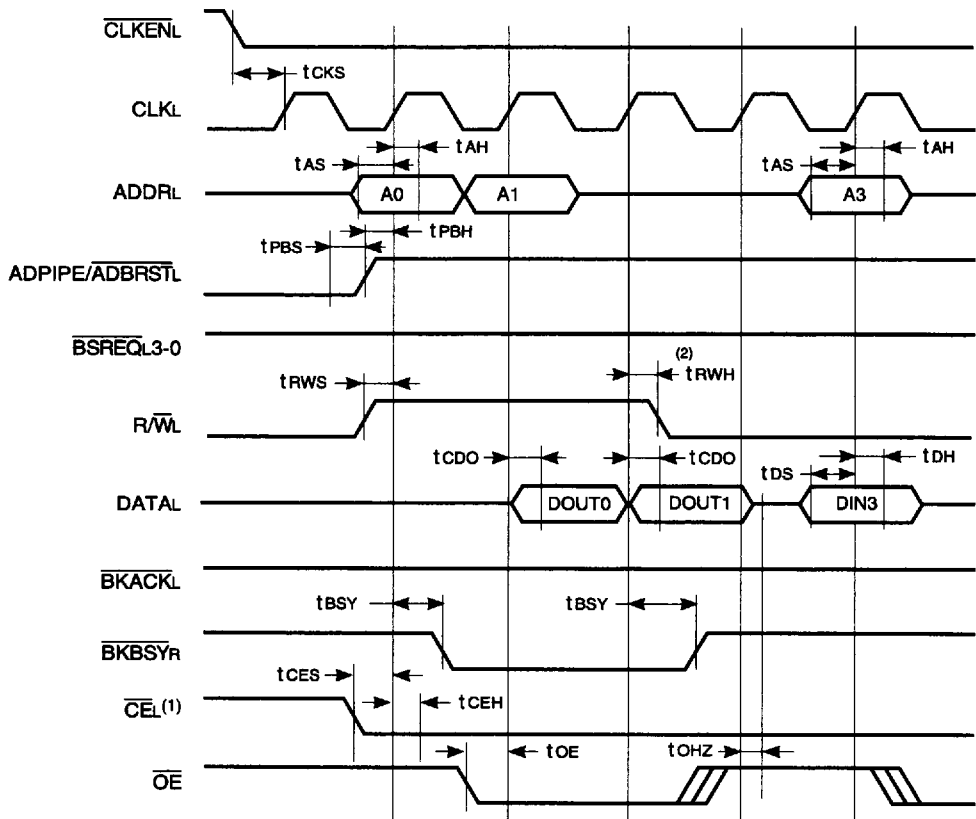
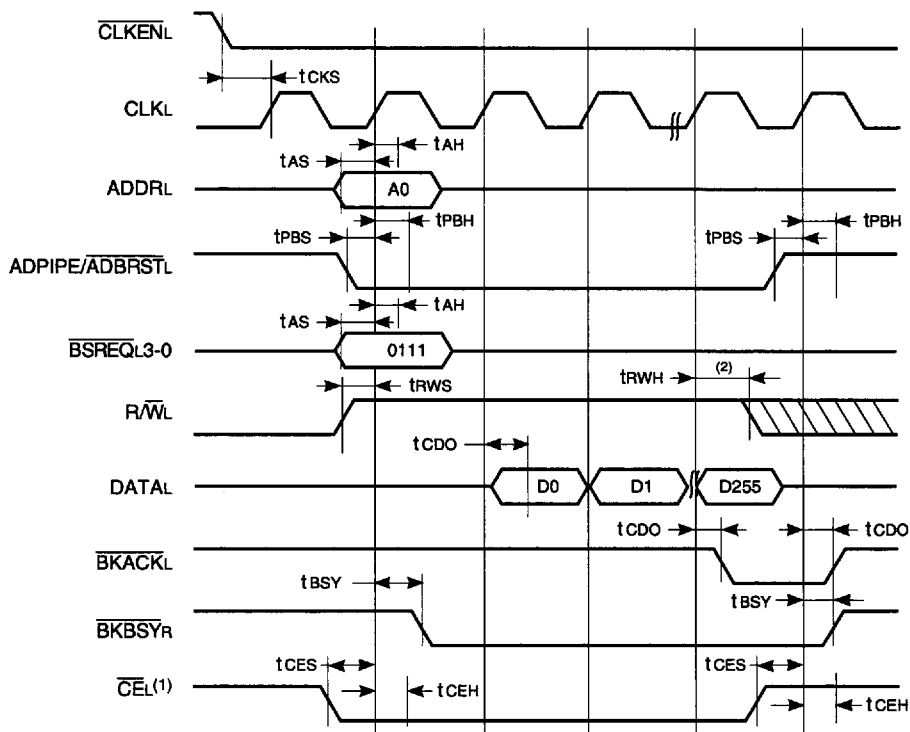


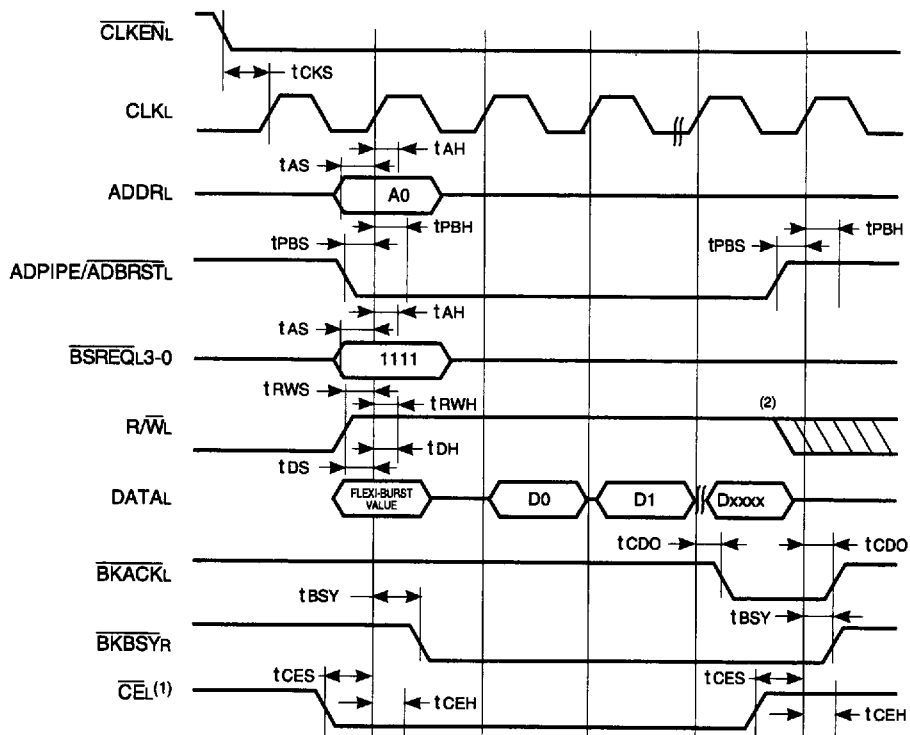
FIGURE 9. BURST READ ONE PORT USING $\overline{CE}$ TO RESET $\overline{BKBSY}$



Notes:

1. If $\overline{CEL} = H$ on the next $CLOCKL$ the $\overline{BKBSYR}$ signals will be reset.
2. Must satisfy t_{RWH} at last burst clock.

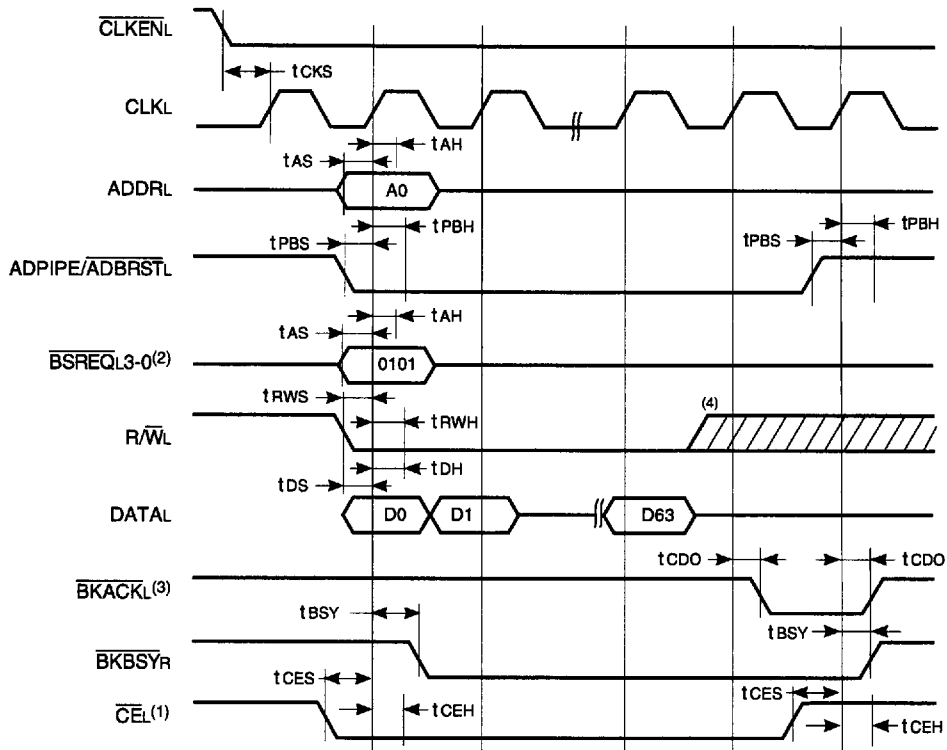
FIGURE 10. FLEXI-BURST READ ONE PORT USING $\overline{CE}$ TO RESET $\overline{BKBSY}$



Notes:

1. If $\overline{CEL} = H$ on the next $CLOCKL$ the $\overline{BKBSYr}$ signals will be reset.
2. Must satisfy t_{RWH} at last burst clock.

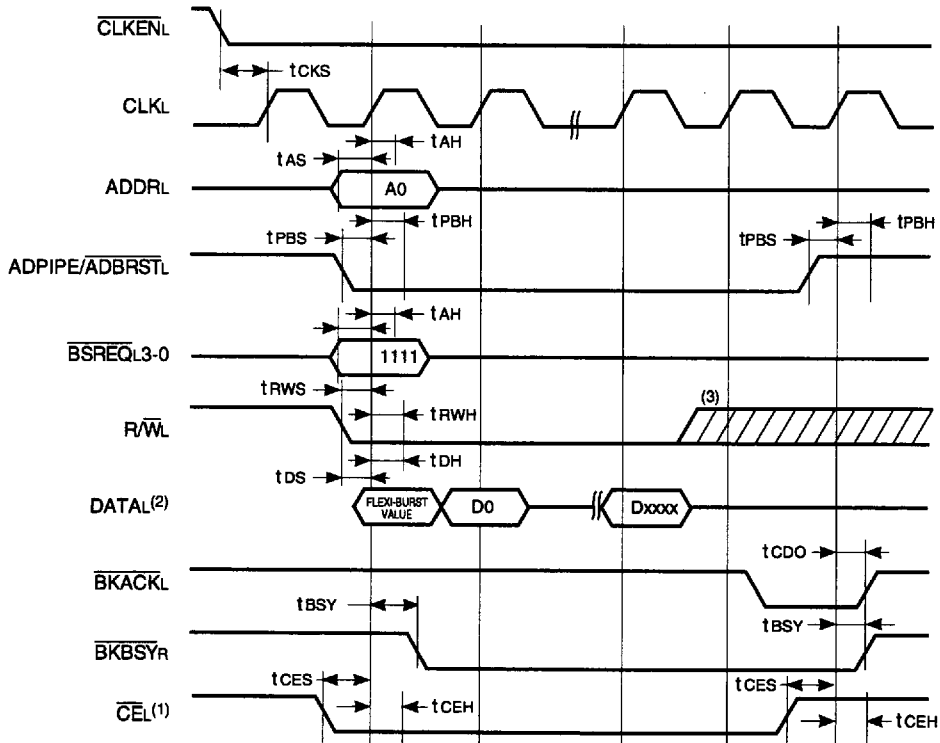
FIGURE 11. BURST WRITE ONE PORT, ONE BLOCK USING $\overline{CE}$ TO RESET $\overline{BKBSY}$



Notes:

1. If $\overline{CEL} = H$ on the next $CLOCKL$ the $\overline{BKBSYr}$ signals will be reset.
2. The burst block size is set up from the BURST BLOCK SIZE TRUTH TABLE, p. 7-6.
3. $\overline{BKACKL}$ going LOW prevents any further burst writes.
4. Must satisfy t_{RWH} at last burst clock.

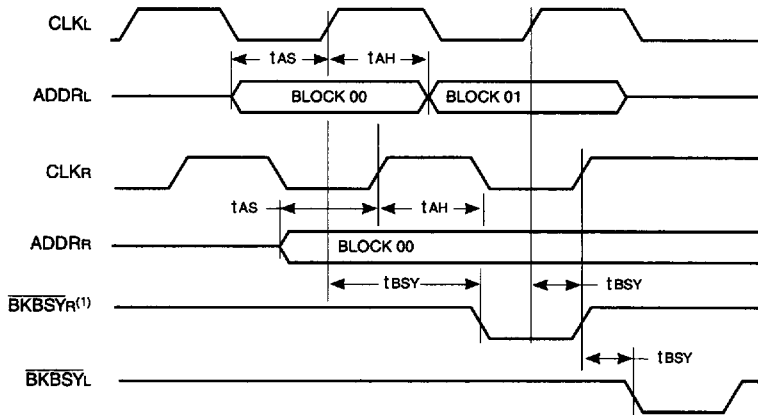
FIGURE 12. FLEXI-BURST WRITE ONE PORT, ONE BLOCK USING $\overline{\text{CE}}$ TO RESET BKBSY



Notes:

1. If $\overline{\text{CEL}} = \text{H}$ on the next CLOCKL the $\overline{\text{BKBSYr}}$ signals will be reset.
2. Binary value placed on data bus D11-D0 sets up burst block size.
3. Must satisfy t_{RWH} at last burst clock.

FIGURE 13. BUSY AND BLOCK ARBITRATION



Note:

1. The address on the left port is clocked before the right port address. Address values are the same. Left port releases control of block address 00 by moving to block address 01. The right port gains access to block address 00 on the second clock.

POWER-ON RESET TRUTH TABLE

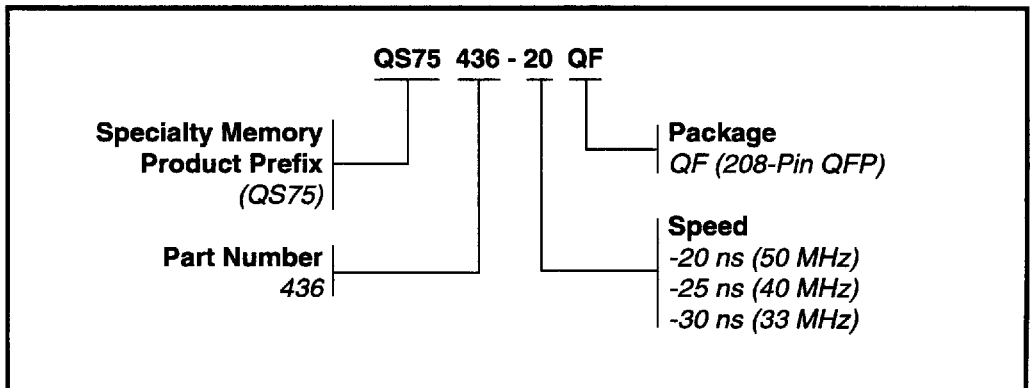
CLKL	CLKR	$\overline{\text{CLKENL}}$	$\overline{\text{CLKENR}}$	$\overline{\text{CEL}}$	$\overline{\text{CER}}$
↑	↑	X	X	H	H

Note:

This must be done to reset the arbitration logic. Port clocks can be coincidental or different.

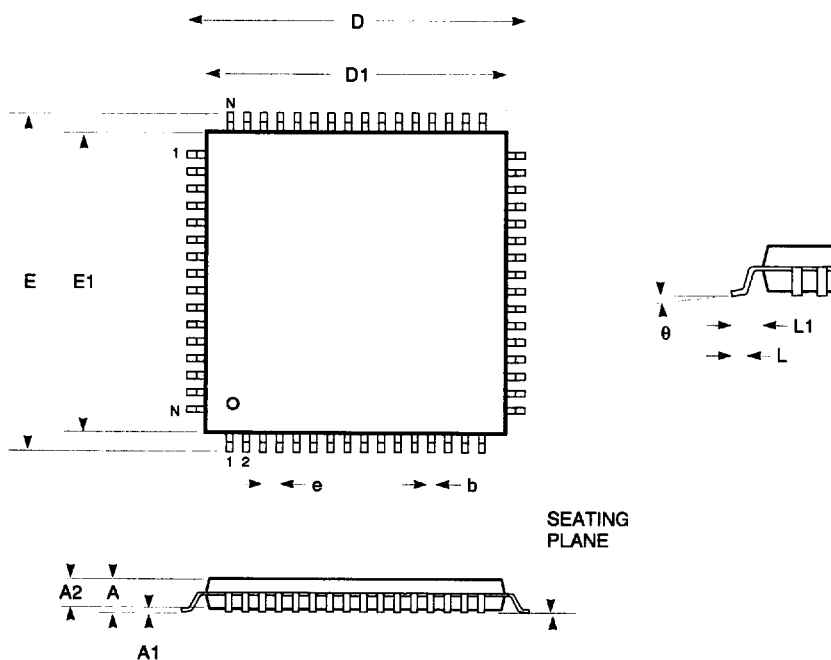
ORDERING INFORMATION

Example:



208-PIN QUAD FLAT PACK (QFP) PACKAGE DRAWING

Counter-clockwise orientation, top view



Notes:

1. Refer to applicable symbol list.
2. All dimensions are in millimeters, unless otherwise specified.
3. Dimensions D1 and E1 do not include mold protrusions. Allowable mold protrusions are:
D1 and E1 = 0.25 Max.
D2 and E2 = 0.17 Max.
5. ND and NE represent number of leads in D and E directions, respectively.

DWG #	QF208	
No. of Leads (N)	208	
Symbols	Min.	Max.
A	—	3.80
A1	0.25	0.45
A2	3.30	3.40
b	0.17	0.23
D	30.40	30.80
D1	27.95	28.05
e	0.45	0.55
E	30.40	30.80
E1	27.95	28.05
L	0.40	0.60
L1	1.20	1.40
θ	0°	10°
ND/NE	52/52	